

**FLOATING BODY TRANSISTOR CONSTRUCTIONS, SEMICONDUCTOR
CONSTRUCTIONS, AND METHODS OF FORMING SEMICONDUCTOR
CONSTRUCTIONS**

ABSTRACT

The invention includes floating body transistor constructions containing U-shaped semiconductor material slices. The U-shapes have a pair of prongs joined to a central portion. Each of the prongs contains a source/drain region of a pair of gatedly-coupled source/drain regions, and the floating bodies of the transistors are within the central portions. The semiconductor material slices can be between front gates and back gates. The floating body transistor constructions can be incorporated into memory arrays, which in turn can be incorporated into electronic systems. The invention also includes methods of forming floating body transistor constructions, and methods of incorporating floating body transistor constructions into memory arrays.

FIGURE 38